				mine of the
L Number	Hits		DB	Time stamp
1	248166	(silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:39
2	104	capicator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:42
3	127590	(transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)		2002/06/25 07:43
4	500125	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:43
5	22767	((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:44
6	15641		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:45
7	730133	polysilicon poly\$9 polycrystallins	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:47
8	8610	<pre>(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:48
9	302791	barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:53
10	16210	((platinumn pt) with (rhodium rh))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:53
11	356	((ruthenium ru) with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 07:53
12	5912	(tungsten w) adj4 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:54

		((///hammister himolar /hi adi nolar) · -	USPAT;	2002/06/25
13	2927	(((((transistor bipolar (bi adj polar) · · · mosfet mos (metal adj oxide) drain	US-PGPUB;	07:54
		mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas	EPO; JPO;	
		ge ((si silicon) adj4 sapphire)) with	DERWENT;	
		ge ((si silicon) adj4 sapphile) with substrate)) and capacitor) and (via plug	IBM TDB	
		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
]	((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))		
1.4	226	((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
14	226	mosfet mos (metal adj oxide) drain	US-PGPUB;	08:33
		source) and ((silicon si germanium gaas	EPO; JPO;	
		ge ((si silicon) adj4 sapphire)) with	DERWENT;	
		substrate)) and capacitor) and (via plug	IBM TDB	
1	1	hole)) and (polysilicon poly\$9	_	
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
	1	((ruthenium ru) with silicide))) and (
1		((platinumn pt) with (rhodium rh)))		
1.5	74	((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
15	/4	mosfet mos (metal adj oxide) drain	US-PGPUB;	08:33
]	1	source) and ((silicon si germanium gaas	EPO; JPO;	1
	1	ge ((si silicon) adj4 sapphire)) with	DERWENT;	
		substrate)) and capacitor) and (via plug	IBM TDB	
1		hole)) and (polysilicon poly\$9	_	
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and (
		((ruthenium ru) with silicide))		
16	386	((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
•	1	mosfet mos (metal adj oxide) drain	US-PGPUB;	08:33
		source) and ((silicon si germanium gaas	EPO; JPO;	
		ge ((si silicon) adj4 sapphire)) with	DERWENT;	
		substrate)) and capacitor) and (via plug	IBM_TDB	
		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier	1	
Ì		((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and		
	•	((tungsten w) adj4 nitride)		
17	35	((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
1 -		mosfet mos (metal adj oxide) drain	US-PGPUB;	08:33
1		source) and ((silicon si germanium gaas	EPO; JPO;	
1		lge ((si silicon) adj4 sapphire)) with	DERWENT;	
		substrate)) and capacitor) and (via plug	IBM_TDB	
1		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and		
		(((((((transistor bipolar (bi adj polar)		
		mosfet mos (metal adj oxide) drain		
1	-	source) and ((silicon si germanium gaas		
1		ge ((si silicon) adj4 sapphire)) with		
		substrate)) and capacitor) and (via plug		
		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
	1	((ruthenium ru) with silicide))) and (
		((ruthenium ru) with silicide))) and		
		((((((transistor bipolar (bi adj polar)		
		mosfet mos (metal adj oxide) drain		
	1	source) and ((silicon si germanium gaas		
		ge ((si silicon) adj4 sapphire)) with		1
		substrate)) and capacitor) and (via plug		1
1		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))	1	
		((ruthenium ru) with silicide))) and		
l	1	((tungsten w) adj4 nitride))	<u> </u>	<u></u>

18	16	((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
10	10	mosfet mos (metal adj oxide) drain	US-PGPUB;	08:34
	1	source) and ((silicon si germanium gaas	EPO; JPO;	
		ge ((si silicon) adj4 sapphire)) with	DERWENT;	
		substrate)) and capacitor) and (via plug	IBM TDB	
		hole)) and (polysilicon poly\$9	-	
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and		
		(((((((transistor bipolar (bi adj polar)		
		mosfet mos (metal adj oxide) drain		
1		source) and ((silicon si germanium gaas		
		ge ((si silicon) adj4 sapphire)) with		
		substrate)) and capacitor) and (via plug		
		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
		((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and (
		((ruthenium ru) with silicide))) and		
		((((((transistor bipolar (bi adj polar)		
	ļ	mosfet mos (metal adj oxide) drain		!
		source) and ((silicon si germanium gaas		
	•	ge ((si silicon) adj4 sapphire)) with		
		substrate)) and capacitor) and (via plug		
		hole)) and (polysilicon poly\$9		
		polycrystallins)) and (barrier		
	1	((platinumn pt) with (rhodium rh))		1
	1	((ruthenium ru) with silicide))) and		
		((tungsten w) adj4 nitride))) and		
		((((((transistor bipolar (bi adj polar)	ļ	
1		mosfet mos (metal adj oxide) drain		
		source) and ((silicon si germanium gaas		
		ge ((si silicon) adj4 sapphire)) with		1
		substrate)) and capacitor) and (via plug-		
		hole)) and (polysilicon poly\$9	ł	
		polycrystallins)) and (barrier		
	[((platinumn pt) with (rhodium rh))		
		((ruthenium ru) with silicide))) and (
1	1	((platinumn pt) with (rhodium rh))))	<u> </u>	

Source and (silicon si germanium gass ge (si silicon) addy sapphire) with substrate) and capacitor) and (via plug hole) and (polysilicon polysy polycrystalins) and (barrier (pierwine) with silicide)) and (((((((transitor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and (silicon si germanium gass ge (si silicon) addy sapphire) with substrate) and capacitor) and (via plug hole) and ((((((((transitor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gass ge (si silicon) addy sapphire) with substrate) and capacitor) and (via plug hole) and (((((((((transitor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gass ge (si silicon) addy sapphire)) with substrate) and capacitor) and (via plug hole) polycrystalins)) and (barrier ((platinum pt) with (thedium rh)) (((((((transitor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and (silicon si germanium gass ge (si silicon) si germanium gass ge (si silicon) with (rhodium rh)) ((((((transitor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and (silicon si germanium gass ge (si silicon) adj sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polysy polycrystalins)) and (barrier ((platinum rh) with (rhodium rh)) (((((((transitor bipolar (bi adj polar)) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gass ge ((si silicon) adj sapphire)) with soubstrate) and capacitor) and (via plug hole) and (polysilicon polysy polycrystalins)) and (barrier ((platinum rh) with (rhodium rh)) (((((((transitor bipolar (bi adj polar)) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gass ge ((si silicon) adj sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polysy polycrystalins) and (bipolar (bi adj polar)) and (2002 (06 /25
source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystalins)) and (barrier ((piatinum pp) with silicide)) and (((((((((transistor bipolar (bi ady polar) mosfer mos (metal ady oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystalins)) and ((((((transistor bipolar (bi ady polar) mosfer mos (metal ady oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with ((((((transistor bipolar (bi ady polar) mosfer mos (metal ady oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with substrate) and capacitor) and (via plug hole)) and (((((((((transistor bipolar (bi ady polar) mosfer mos (metal ady oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with substrate) and capacitor) and (via plug hole) and polysilicon polys) polycrystalins) and (barrier ((piatinum pi) with silicide))) and ((((((((((transistor bipolar (bi ady polar) mosfer mos (metal ady oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adyd sapphire)) with substrate) and capacitor) and (via plug hole) and ((piplar mum pt) with ((rhodium rh)))) and (piplar (bi ady polar)) and (bipolar (bi	19	0	(((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
ge ((si silicon) adj4 sapphire) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and source) and (silicon si germanium gaas ge ((si silicon) adj4 sapphire) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (((ruthenium ru) with silicide)) and ((((ruthenium ru) with silicide)) and ((((((transistor bipolar (bi adj polar)) mosfer nos (metal ad) (sigmanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins) and (barrier ((platinum ru) with silicide)) and ((((((transistor bipolar (bi adj polar)) mosfer nos (metal ad) (germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((platinum pt) with (rhodium rh) ((ruthenium ru) with silicide))) and ((bipolar (bi ad) polar)) (bipolar (bi ad) polar)) (bipolar (bi ad) polar)) (c(((((transintor bipolar (bi ad) polar)) mosfet nos (metal ad) oxide managas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi ad) polar)) (bipolar (bi ad) polar)			mosfet mos (metai ad] oxide) drain		00.54
Substrate) and capacitor) and (via plug hole) and (polysilicon polyš) polycrystallins)) and (barrier (platinum pri with (rhodium rh)) ((ruthenium ru) with silicide)) and (polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire) with substrate) and capacitor) and (via plug hole) and (polysilicon polyš) polycrystallins) and (barrier ((platinum pri with (rhodium rh)) ((ruthenium rui) with silicide)) and (clinicon adj4 sapphire) with mosfet mos (metal adj oxide) drain source) and (silicon si germanium daad ge ((si silicon) adj4 sapphire) with substrate) and capacitor) and (via plug hole)) and (polysilicon polyš) polycrystallins) and (barrier ((platinum pri with (rhodium rh)) ((rutheneum vadj4 nitride))) and ((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole) and (polysilicon polyš) polycrystallins) and (barrier ((platinum pri with (rhodium rh))) and ((((((((transistor bipolar (bi adj polar)) and ((platinum pri with (rhodium rh)))) and (polysilicon polyš) polycrystallins) and (barrier ((platinum pri with (rhodium rh))) and (platinum pri with (rhodium rh))) and (platinum pri with (rhodium rh)) ((((((((transistor bipolar (bi adj polar))))) and ((((((((transistor bipolar (bi adj polar)))))) and (((((((((transistor bipolar))))))) and ((((((((transistor bipolar)))))) and ((((((((transistor bipolar))))))) and ((((((((transistor bipolar)))))))) and (((((((((transistor bipolar))))))))))))))))))))))))))))))))))))			ge ((si silicon) adi4 sapphire)) with		
hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinumn pt) with (rhodium rh) ((utthenium ru) with silicide)) and ((((((((transistor bipolar (bi ad) polar) moefet mos (matal ad) sagenmanum gaas ge ((si silicon) ad) sagenmanum gas ge ((si silicon) ad) sagenmanum hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (((((((transistor bipolar (bi ad) polar) mosfet mos (metal ad) oxide) drain substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (((((((transistor bipolar (bi ad) polar) mosfet mos (metal ad) oxide) drain source) and ((silicon si germanum gas substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((putthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) 22 194 ((((((transistor bipolar (bi ad) polar) mosfet mos (metal ad) oxide) drain source) and (silicon si germanum gas germanum ger	1		substrate)) and capacitor) and (via plug		
polycrystalins) and (barrier ((platinum pro with (thodium rh)) ((ruthenium ru) with silicide)) and ((((((transistor bipolar (bi adj polar)) mosfet mos (metal adj oxide) drain source) and (silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug help polycrystallins)) and (barrier ((platinum pro with (thodium rh)) ((ruthenium ru) with silicide)) and (((((((transistor bipolar (bi adj polar)) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hele) and (polysilicon poly59 polycrystallins)) and (barrier ((((transistor bipolar (bi adj polar)) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hele) and (polysilicon poly59 polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((platinum pt) with (rhodium rh)) ((platinum pt) with (rhodium rh)) ((platinum pt) with (rhodium rh) ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) an				_	:
((platinum pt) with (rhodium rh) ((ruthenium ru) with silicide)) and ((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire) with substrate)) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins) and (bactium rh) ((ruthenium ru) with silicide)) and ((((((ttransistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium daas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon polys) polycrystallins) and (barrier ((platinum) pt) with (rhodium rh) ((ruthenium ru) with silicide)) and ((((((ttransistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain substrate)) and capacitor) and (via plug hole) and (polysilicon polys) polycrystallins)) and (barrier ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) ((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon polys) polycrystallins) and (barrier ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) (((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon polys) polycrystallins)) and (barrier ((platinum) pt) with (rhodium rh) ((ruthenium ru) with silicide)) (((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) ((platinum) pt) with (rhodium rh) ((ruthenium ru) with silicide)) (((((((transisto					
((ruthenium ru) with silicide)) and ((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (((((((transistor bipolar (bi adj polar) mosfet mos (ros) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (polysilicon polys9 polycrystallins)) and (barrier ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ((platinum) pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) (((((((transistor bipolar (bi adj polar) nonfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and (bipolar (bi adj polar)) source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 pol			((platinumn pt) with (rhodium rh))		
source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and (applysilicon polys9 polycrystallins) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((((((((ruthenium ru) with silicide))) and (((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with ((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide))) and (((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide))) and (((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide))) and ((((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide))))) and (((((((((((transistor bipolar (bi adj polar) mosfet mos (metal ad) oxide))))))))))))))))))))))))))))))))))))	1		((ruthenium ru) with silicide))) and		
ge (isi silicon) adiy asphire)) with substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((((((((transistor bipolar (bi adi polar) mosfet mos (metal ad) oxide) drain source) and ((silicon si germanium gaas ge (isi silicon) adiy asphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon polys9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((tungsten with a content of the co					
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substrate) and capacitor) and (via plug hole) and (polysilicon polys9 polycrystallins)) and (barrier ([platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge (si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon polys9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((tungsterw) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon polys9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)) and ((platinumn pt) with (rhodium rh)) (platinumn pt) with (plat			source) and ((silicon si germanium gaas		i
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(bipolar (bi adj polar))) and ((tungsten w) adj4 nitride) ((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))			((platinumn pt) with (rhodium rh))		
w) adj4 nitride) (((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))					
22 194 (((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))					
mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))	22	194		USPAT;	2002/06/25
source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))			mosfet mos (metal adj oxide) drain	·	· ·
ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))			source) and ((silicon si germanium gaas	EPO; JPO;	
hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))			ge ((si silicon) adj4 sapphire)) with		
polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh))				IBM_TDB	
((platinumn pt) with (rhodium rh))					
	j				
i i i i i i i i i i i i i i i i i i i		ĺ	((ruthenium ru) with silicide))) and		
(bipolar (bi adj polar))) and "111"	[]				

23 258 ((((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 IBM_TDB);
source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with DERWENT; substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9);
ge ((si silicon) adj4 sapphire)) with DERWENT; substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9	· 1
substrate)) and capacitor) and (via plug IBM_TDB hole)) and (polysilicon poly\$9	
hole)) and (polysilicon poly\$9	
hole)) and (polysilicon poly\$9	
polycrystallins)) and (barrier	!
((platinumn pt) with (rhodium rh))	
((ruthenium ru) with silicide))) and	
(bipolar (bi adj polar))) and "110"	
24 4 ((((((transistor bipolar (bi adj polar) USPAT;	2002/06/25
source) and ((silicon si germanium gaas EPO; JPC	
ge ((si silicon) adj4 sapphire)) with DERWENT;	
substrate)) and capacitor) and (via plug IBM_TDB	
hole)) and (polysilicon poly\$9	
polycrystallins)) and (barrier	
((platinumn pt) with (rhodium rh))	
((ruthenium ru) with silicide))) and	
(bipolar (bi adj polar))) and (
((ruthenium ru) with silicide))	
25 17 ((((((transistor bipolar (bi adj polar) USPAT;	2002/06/25
mosfet mos (metal adj oxide) drain US-PGPUB	
source) and ((silicon si germanium gaas EPO; JPO	
ge ((si silicon) adj4 sapphire)) with DERWENT;	
substrate)) and capacitor) and (via plug IBM_TDB	
hole)) and (polysilicon poly\$9	
polycrystallins)) and (barrier	
((platinumn pt) with (rhodium rh))	
((ruthenium ru) with silicide))) and	
(bipolar (bi adj polar))) and (
((platinumn pt) with (rhodium rh)) · •	
26 4 (((((((transistor bipolar (bi adj polar) USPAT;	2002/06/25
mosfet mos (metal adj oxide) drain US-PGPUB	
source) and ((silicon si germanium gaas EPO; JPO	,
ge ((si silicon) adj4 sapphire)) with DERWENT;	
substrate)) and capacitor) and (via plug IBM_TDB	
hole)) and (polysilicon poly\$9	
polycrystallins)) and (barrier	
((platinumn pt) with (rhodium rh))	
((ruthenium ru) with silicide))) and	
(bipolar (bi adj polar))) and ((tungsten	
w) adj4 nitride)) and ((((((transistor	1
bipolar (bi adj polar) mosfet mos (metal	
adj oxide) drain source) and ((silicon si	
germanium gaas ge ((si silicon) adj4	
sapphire)) with substrate)) and	
capacitor) and (via plug hole)) and	
(polysilicon poly\$9 polycrystallins)) and	1
(barrier ((platinumn pt) with (rhodium	
	1
rh)) ((ruthenium ru) with silicide))) and	
(bipolar (bi adj polar))) and (
((platinumn pt) with (rhodium rh)))	<u> </u>

27	0 (((((((transistor bipolar (bi adj polar)	USPAT;	2002/06/25
21	mosfet mos (metal adj oxide) drain	US-PGPUB;	08:36
	source) and ((silicon si germanium gaas	EPO; JPO;	
i	ge ((si silicon) adj4 sapphire)) with	DERWENT;	
	substrate)) and capacitor) and (via plug	IBM TDB	
	hole)) and (polysilicon poly\$9	_	1
	polycrystallins)) and (barrier		
	((platinumn pt) with (rhodium rh))		
1	((ruthenium ru) with silicide))) and		1
	(bipolar (bi adj polar))) and (
	((ruthenium ru) with silicide))) and		
	((((((((transistor bipolar (bi adj		
i	polar) mosfet mos (metal adj oxide)		
	drain source) and ((silicon si germanium		
	gaas ge ((si silicon) adj4 sapphire))		
	with substrate)) and capacitor) and (via		
	plug hole)) and (polysilicon poly\$9		
	polycrystallins)) and (barrier		
	((platinumn pt) with (rhodium rh))		
	((ruthenium ru) with silicide))) and .	-	
	(bipolar (bi adj polar))) and ((tungsten		
i	w) adj4 nitride)) and ((((((transistor		1
	bipolar (bi adj polar) mosfet mos (metal		
	adj oxide) drain source) and ((silicon si		
	germanium gaas ge ((si silicon) adj4		
	sapphire)) with substrate)) and	}	
	capacitor) and (via plug hole)) and	1	
	(polysilicon poly\$9 polycrystallins)) and	i	
	(barrier ((platinumn pt) with (rhodium		
	rh)) ((ruthenium ru) with silicide))) and	i	
	(bipolar (bi adj polar))) and (-	•
	(plotal (b) adj polal)) and (1
	((platinumn pt) with (rhodium rh))))		